

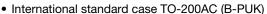
Phase Control Thyristors (Hockey PUK Version), 790 A



TO-200AC (B-PUK)

FEATURES

- Center amplifying gate
- Metal case with ceramic insulator





 Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- DC motor control
- Controlled DC power supplies
- AC controllers

| PRODUCT SUMMARY | | | | |
|------------------------------------|------------------------|--|--|--|
| Package | TO-200AC (B-PUK) | | | |
| Diode variation | Single SCR | | | |
| I _{T(AV)} | 790 A | | | |
| V _{DRM} /V _{RRM} | 2000 V, 2200 V, 2400 V | | | |
| V_{TM} | 2.07 V | | | |
| I _{GT} | 100 mA | | | |
| T_J | -40 °C to 125 °C | | | |

| MAJOR RATINGS AND CHARACTERISTICS | | | | | |
|------------------------------------|-----------------|--------------|-------------------|--|--|
| PARAMETER | TEST CONDITIONS | VALUES | UNITS | | |
| 1 | | 790 | A | | |
| I _{T(AV)} | T _{hs} | 55 | °C | | |
| I _{T(RMS)} | | 1557 | A | | |
| | T _{hs} | 25 | °C | | |
| I _{TSM} | 50 Hz | 10 100 | Δ. | | |
| | 60 Hz | 10 700 | A | | |
| l ² t | 50 Hz | 510 | kA ² s | | |
| I=[| 60 Hz | 475 | KA ^z S | | |
| V _{DRM} /V _{RRM} | | 2000 to 2400 | V | | |
| tq | Typical | 200 | μs | | |
| T _J | | -40 to 125 | °C | | |

ELECTRICAL SPECIFICATIONS

| VOLTAGE RATINGS | | | | | | | | |
|-----------------|-----------------|--|--|---|--|--|--|--|
| TYPE NUMBER | VOLTAGE CODE | V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V | V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V | I_{DRM}/I_{RRM} MAXIMUM AT T _J = T _J MAXIMUM mA | | | | |
| | 20 | 2000 | 2100 | | | | | |
| VS-ST650CL 22 | | 2200 | 2300 | 80 | | | | |
| | 24 | 2400 | 2500 | | | | | |



| PARAMETER | SYMBOL | TEST CONDITIONS | | | VALUES | UNITS | | | |
|---|---------------------|--|--|-----------------------------|--------|---------------------------------|--|-----------|---|
| Maximum average on-state current | | 180° condu | 180° conduction, half sine wave Double side (single side) cooled | | | 180° conduction, half sine wave | | 790 (324) | Α |
| at heatsink temperature | I _{T(AV)} | Double side | | | | °C | | | |
| Maximum RMS on-state current | I _{T(RMS)} | DC at 25 °C | DC at 25 °C heatsink temperature double side cooled | | | | | | |
| | | t = 10 ms | No voltage | | 10 100 | | | | |
| Maximum peak, one-cycle | | t = 8.3 ms | reapplied | | 10 700 | А | | | |
| non-repetitive surge current | I _{TSM} | t = 10 ms | 100 % V _{RRM} | | 8600 | | | | |
| | | t = 8.3 ms | reapplied | Sinusoidal half wave, | 9150 | | | | |
| Maximum I ² t for fusing | | t = 10 ms No voltage | No voltage | initial $T_J = T_J$ maximum | 510 | - kA ² s | | | |
| | l ² t | t = 8.3 ms | reapplied | | 475 | | | | |
| | I-I | t = 10 ms | 100 % V _{RRM} | | 370 | | | | |
| | | t = 8.3 ms | reapplied | | 347 | | | | |
| Maximum I ² √t for fusing | I ² √t | t = 0.1 to 10 ms, no voltage reapplied | | | 5100 | kA²√s | | | |
| Low level value of threshold voltage | V _{T(TO)1} | (16.7 % x π | (16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum | | | V | | | |
| High level value of threshold voltage | V _{T(TO)2} | $(I > \pi \times I_{T(AV)})$ | $(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$ | | | V | | | |
| Low level value of on-state slope resistance | r _{t1} | (16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum | | | 0.61 | mΩ | | | |
| High level value of on-state slope resistance | r _{t2} | $(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$ | | | 0.35 | 11152 | | | |
| Maximum on-state voltage | V _{TM} | $I_{pk} = 1700 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$ | | | 2.07 | V | | | |
| Maximum holding current | I _H | T 05 00 | T 25.00 1 1.40 1 1 1 1 | | | A | | | |
| Typical latching current | IL | T _J = 25 °C, anode supply 12 V resistive load | | | 1000 | mA | | | |

| SWITCHING | | | | | | | |
|--|----------------|--|--------|-------|--|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS | | | |
| Maximum non-repetitive rate of rise of turned-on current | dl/dt | Gate drive 20 V, 20 Ω , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$ | 1000 | A/μs | | | |
| Typical delay time | t _d | Gate current 1 A, $dl_g/dt = 1$ A/ μ s $V_d = 0.67 \% V_{DRM}$, $T_J = 25 °C$ | 1.0 | us | | | |
| Maximum turn-off time | t _q | I_{TM} = 750 A, T_J = T_J maximum, dI/dt = 60 A/μs V_R = 50, dV/dt = 20 V/μs, Gate 0 V 100 Ω , t_p = 500 μs | 200 | μο | | | |

| BLOCKING | | | | |
|--|--|--|--------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
| Maximum critical rate of rise of off-state voltage | dV/dt | $T_J = T_J$ maximum linear to 80 % rated V_{DRM} | 500 | V/µs |
| Maximum peak reverse and off-state leakage current | I _{RRM} , I _{DRM} | $T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied | 80 | mA |



| TRIGGERING | | | | | | | |
|-------------------------------------|--------------------|-------------------------|--|------|--------|-------|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | | | VALUES | | |
| FANAMETEN | STWIBOL | 15 | 31 CONDITIONS | typ. | max. | UNITS | |
| Maximum peak gate power | P_{GM} | $T_J = T_J$ maximum, | t _p ≤ 5 ms | 10.0 | | W | |
| Maximum average gate power | P _{G(AV)} | $T_J = T_J$ maximum, | f = 50 Hz, d% = 50 | 2 | .0 | VV | |
| Maximum peak positive gate current | I _{GM} | | | 3 | .0 | Α | |
| Maximum peak positive gate voltage | + V _{GM} | $T_J = T_J$ maximum, | $T_J = T_J$ maximum, $t_p \le 5$ ms | | | V | |
| Maximum peak negative gate voltage | - V _{GM} | , | | | .0 | V | |
| DC gate current required to trigger | I _{GT} | T _J = -40 °C | | 200 | - | | |
| | | T _J = 25 °C | | 100 | 200 | mA | |
| | | T _J = 125 °C | Maximum required gate trigger/ current/voltage are the lowest | 50 | - | 1 | |
| | | T _J = -40 °C | value which will trigger all units 12 V anode to cathode applied | 2.5 | - | | |
| DC gate voltage required to trigger | V_{GT} | T _J = 25 °C | 12 v anode to camode applied | 1.8 | 3.0 | V | |
| | | T _J = 125 °C | | 1.1 | - | | |
| DC gate current not to trigger | I _{GD} | T T | Maximum gate current/voltage not to trigger is the maximum | 10 | | mA | |
| DC gate voltage not to trigger | V _{GD} | $T_J = T_J$ maximum | value which will not trigger any unit with rated V _{DRM} anode to cathode applied | 0. | 25 | V | |

| THERMAL AND MECHANICAL SPECIFICATIONS | | | | | | |
|--|---------------------|---|------------------|-----------|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS | | |
| Maximum operating temperature range | TJ | | -40 to 125 | °C | | |
| Maximum storage temperature range | T _{Stg} | | -40 to 150 | | | |
| Maximum thermal resistance, junction to heatsink | R _{thJ-hs} | DC operation single side cooled | 0.073 | | | |
| | | DC operation double side cooled | 0.031 | K/W | | |
| Maximum thornal registeres ages to be stein! | R _{thC-hs} | DC operation single side cooled | 0.011 | N/ VV | | |
| Maximum thermal resistance, case to heatsink | | DC operation double side cooled | 0.006 | | | |
| Mounting force, ± 10 % | | | 14 700 (1500) | N (kg) | | |
| Approximate weight | | | 255 | g | | |
| Case style | | See dimensions - link at the end of datasheet | TO-200AC (| (B-PUK) | | |

| △R _{thJ-hs} CONDUCTION | | | | | | |
|---------------------------------|-------------|--------------------------------------|-------------|-------------|---------------------|-------|
| CONDUCTION ANGLE | SINUSOIDAL | AL CONDUCTION RECTANGULAR CONDUCTION | | CONDUCTION | TEST CONDITIONS | UNITS |
| CONDUCTION ANGLE | Single Side | Double Side | Single Side | Double Side | TEST CONDITIONS | UNITS |
| 180° | 0.009 | 0.009 | 0.006 | 0.006 | $T_J = T_J$ maximum | |
| 120° | 0.011 | 0.011 | 0.011 | 0.011 | | |
| 90° | 0.014 | 0.014 | 0.015 | 0.015 | | K/W |
| 60° | 0.020 | 0.020 | 0.021 | 0.021 | | |
| 30° | 0.036 | 0.036 | 0.036 | 0.036 | | |

Note

• The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

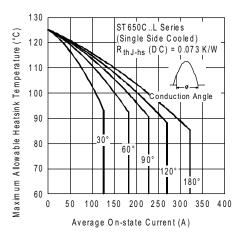


Fig. 1 - Current Ratings Characteristics

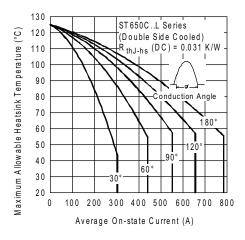


Fig. 2 - Current Ratings Characteristics

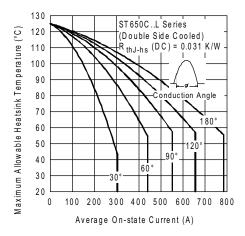


Fig. 3 - Current Ratings Characteristics

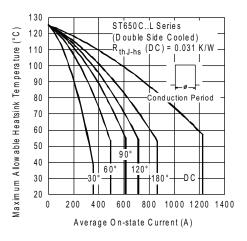


Fig. 4 - Current Ratings Characteristics

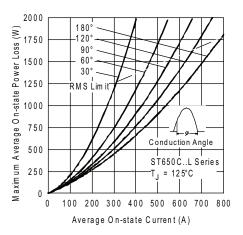


Fig. 5 - On-State Power Loss Characteristics

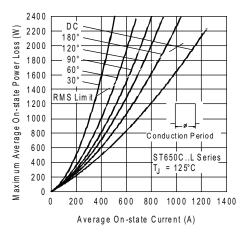


Fig. 6 - On-State Power Loss Characteristics

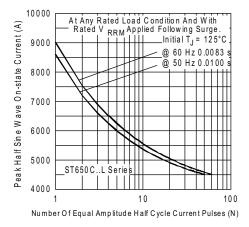


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

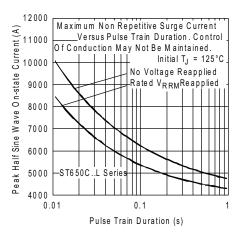


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

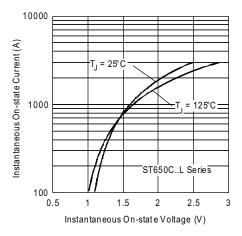


Fig. 9 - On-State Voltage Drop Characteristics

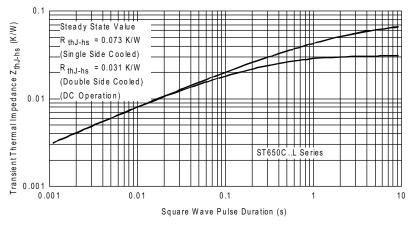


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

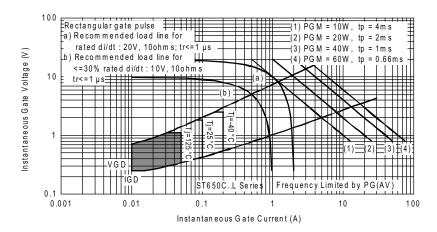
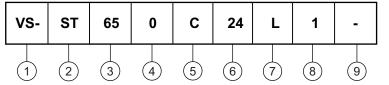


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- 2 Thyristor
- 3 Essential part number
- 4 0 = Converter grade
- 5 C = Ceramic PUK
- 6 Voltage code x 100 = V_{RRM} (see Voltage Ratings table)
- 7 L = PUK case TO-200AC (B-PUK)
- 8 0 = Eyelet terminals (gate and auxiliary cathode unsoldered leads)
 - 1 = Fast-on terminals (gate and auxiliary cathode unsoldered leads)
 - 2 = Eyelet terminals (gate and auxiliary cathode soldered leads)
 - 3 = Fast-on terminals (gate and auxiliary cathode soldered leads)
- 9 Critical dV/dt: None = 500 V/µs (standard selection)
 - L = 1000 V/µs (special selection)

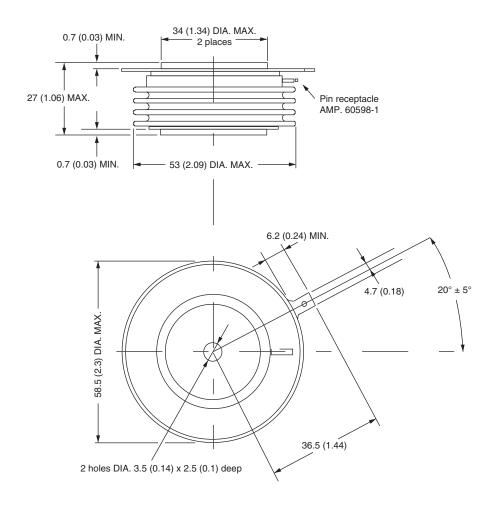
| LINKS TO RELATED DOCUMENTS | | | | |
|----------------------------|--------------------------|--|--|--|
| Dimensions | www.vishay.com/doc?95076 | | | |



TO-200AC (B-PUK)

DIMENSIONS in millimeters (inches)

Creepage distance: 36.33 (1.430) minimum Strike distance: 17.43 (0.686) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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